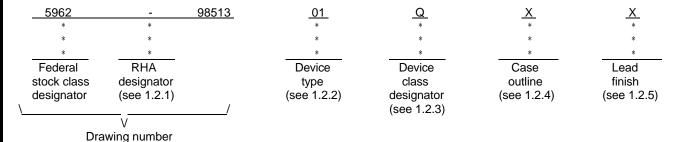
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REV										<u> </u>					<u> </u>	<u> </u>	Ī			
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OF SHEETS				SHE	ET		1	2	3	4	5	6	7	8	9	10	11	12	13	14
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STAN MICRO DRA	CIR	CUI	Т		CKED off Bow															
DRAWING THIS DRAWING IS AVAILABLE FOR USE BY ALL DEPARTMENTS AND AGENCIES OF THE DEPARTMENT OF DEFENSE				ROVE aymon	D BY Id Mon	nin												GATE LICON		
					98-1	2-16	L DAT	E	SIZE	\		SE CO 726			59	62-	98	513)	
AMSC N/A				.5.014	v _	. -			SHE		1		DF	38						

1. SCOPE

- 1.1 <u>Scope</u>. This drawing documents three product assurance class levels consisting of space application (device class V), high reliability (device classes M and Q), and nontraditional performance environment (device class N). A choice of case outlines and lead finishes are available and are reflected in the Part or Identifying Number (PIN). When available, a choice of Radiation Hardness Assurance (RHA) levels are reflected in the PIN. For device class N, the user is cautioned to assure that the device is appropriate for the application environment.
 - 1.2 PIN. The PIN shall be as shown in the following example:



- 1.2.1 <u>RHA designator</u>. Device classes N, Q, and V RHA marked devices meet the MIL-PRF-38535 specified RHA levels and are marked with the appropriate RHA designator. Device class M RHA marked devices meet the MIL-PRF-38535, appendix A specified RHA levels and are marked with the appropriate RHA designator. A dash (-) indicates a non-RHA device.
 - 1.2.2 Device type(s). The device type(s) shall identify the circuit function as follows:

Device type	Generic number	Circuit function	Access time
01	XQ4013XL-3	13000 gate programmable array	3.0 ns

1.2.3 <u>Device class designator</u>. The device class designator shall be a single letter identifying the product assurance level as follows:

Device class	Device requirements documentation
М	Vendor self-certification to the requirements for MIL-STD-883 compliant, non-JAN class level B microcircuits in accordance with MIL-PRF-38535, appendix A
N	Certification and qualification to MIL-PRF-38535 with a non-traditional performance environment encapsulated in plastic
Q or V	Certification and qualification to MIL-PRF-38535

1.2.4 Case outline(s). The case outline(s) are as designated in MIL-STD-1835, JEDEC Publication 95, and as follows:

Outline letter	Descriptive designator	Terminals	Package style
			
Χ	CMGA10-P223	223	Pin grid array package
Υ	See figure 1	228	Quad flat package
Z	See figure 1	228	Quad flat package
U	PBGA-B-256	256	Ball grid array with four rows on each side (plastic)
	(JEDEC MO-151-BAL	2)	
T	PQFP-G-240	240	Quad flat package
	(JEDEC MS-029-GA))	

1.2.5 <u>Lead finish</u>. The lead finish is as specified in MIL-PRF-38535 for device classes N, Q, and V or MIL-PRF-38535, appendix A for device class M.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 2

1.3 Absolute maximum ratings. 1/2/ Thermal resistance, junction-to-case (1_{JC}): Case outlines U ----- 0.8EC/W <u>3</u>/ 1.4 Recommended operating conditions. 1.5 Digital logic testing for device classes N, Q and V. Fault coverage measurement of manufacturing logic tests (MIL-STD-883, test method 5012) ----- 99.9 percent 2. APPLICABLE DOCUMENTS 2.1 Government specification, standards, and handbooks. The following specification, standards, and handbooks form a part of this drawing to the extent specified herein. Unless otherwise specified, the issues of these documents are those listed in the issue of the Department of Defense Index of Specifications and Standards (DoDISS) and supplement thereto, cited in the solicitation. **SPECIFICATION** DEPARTMENT OF DEFENSE MIL-PRF-38535 - Integrated Circuits, Manufacturing, General Specification for. STANDARDS DEPARTMENT OF DEFENSE MIL-STD-883 - Test Method Standard Microcircuits. MIL-STD-973 - Configuration Management. MIL-STD-1835 - Interface Standard For Microcircuit Case Outlines. **HANDBOOKS** DEPARTMENT OF DEFENSE MIL-HDBK-103 - List of Standard Microcircuit Drawings (SMD's). MIL-HDBK-780 - Standard Microcircuit Drawings. (Unless otherwise indicated, copies of the specification, standards, and handbooks are available from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.) All voltage values in this drawing are with respect to V_{SS} Stresses above the absolute maximum rating may cause permanent damage to the device. Extended operation at the maximum levels may degrade performance and affect reliability. When a thermal resistance for this case is specified in MIL-STD-1835 that value shall supersede the value indicated herein. Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions in accordance with method 5004 of MIL-STD-883.

STANDARD
MICROCIRCUIT DRAWING
DEFENSE SUPPLY CENTER COLUMBUS
COLUMBUS, OHIO 42316-5000

SIZE A		5962-98513
	REVISION LEVEL	SHEET 3

2.2 <u>Non-Government publications</u>. The following documents form a part of this document to the extent specified herein. Unless otherwise specified, the issues of the documents which are DoD adopted are those listed in the issue of the DODISS cited in the solicitation. Unless otherwise specified, the issues of documents not listed in the DODISS are the issues of the documents cited in the solicitation.

AMERICAN SOCIETY FOR TESTING AND MATERIALS (ASTM)

ASTM Standard F1192-88 - Standard Guide for the Measurement of Single Event Phenomena from Heavy Ion Irradiation of Semiconductor Devices.

(Applications for copies of ASTM publications should be addressed to the American Society for Testing and Materials, 1916 Race Street, Philadelphia, PA 19103.)

ELECTRONICS INDUSTRIES ALLIANCE (EIA)

JEDEC Standard No. 17 -

A Standardized Test Procedure for the Characterization of Latch-up in CMOS Integrated Circuits.

JEDEC Publication 95

Registered and Standard Outlines for Semiconductor Devices

(Applications for copies should be addressed to the Electronics Industries Alliance, 2500 Wilson Blvd., Arlington, VA 22201.

(Non-Government standards and other publications are normally available from the organizations that prepare or distribute the documents. These documents also may be available in or through libraries or other informational services.)

2.3 <u>Order of precedence</u>. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

- 3.1 <u>Item requirements</u>. The individual item requirements for device classes N, Q, and V shall be in accordance with MIL-PRF-38535 and as specified herein or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. The individual item requirements for device class M shall be in accordance with MIL-PRF-38535, appendix A for non-JAN class level B devices and as specified herein.
- 3.2 <u>Design, construction, and physical dimensions</u>. The design, construction, and physical dimensions shall be as specified in MIL-PRF-38535 and herein for device classes N, Q, and V or MIL-PRF-38535, appendix A and herein for device class M.
 - 3.2.1 Case outline(s). The case outline(s) shall be in accordance with 1.2.4 herein and figure 1.
 - 3.2.2 <u>Terminal connections</u>. The terminal connections shall be as specified on figure 2.
 - 3.2.3 Logic block diagram. The logic block diagram shall be as specified on figure 3.
- 3.3 <u>Electrical performance characteristics and postirradiation parameter limits</u>. Unless otherwise specified herein, the electrical performance characteristics and postirradiation parameter limits are as specified in table I and shall apply over the full case operating temperature range.
- 3.4 <u>Electrical test requirements</u>. The electrical test requirements shall be the subgroups specified in table IIA. The electrical tests for each subgroup are defined in table I.
- 3.5 Marking. The part shall be marked with the PIN listed in 1.2 herein. In addition, the manufacturer's PIN may also be marked as listed in MIL-HDBK-103. For packages where marking of the entire SMD PIN number is not feasible due to space limitations, the manufacturer has the option of not marking the "5962-" on the device. For RHA product using this option, the RHA designator shall still be marked. Marking for device classes N, Q, and V shall be in accordance with MIL-PRF-38535. Marking for device class M shall be in accordance with MIL-PRF-38535, appendix A.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 4

- 3.5.1 <u>Certification/compliance mark</u>. The certification mark for device classes N, Q, and V shall be a "QML" or "Q" as required in MIL-PRF-38535. The compliance mark for device class M shall be a "C" as required in MIL-PRF-38535, appendix A.
- 3.6 <u>Certificate of compliance</u>. For device classes N, Q, and V, a certificate of compliance shall be required from a QML-38535 listed manufacturer in order to supply to the requirements of this drawing (see 6.6.1 herein). For device class M, a certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in MIL-HDBK-103 (see 6.6.2 herein). The certificate of compliance submitted to DSCC-VA prior to listing as an approved source of supply for this drawing shall affirm that the manufacturer's product meets, for device classes N, Q, and V, the requirements of MIL-PRF-38535 and herein or for device class M, the requirements of MIL-PRF-38535, appendix A and herein.
- 3.7 <u>Certificate of conformance</u>. A certificate of conformance as required for device classes N, Q, and V in MIL-PRF-38535 or for device class M in MIL-PRF-38535, appendix A shall be provided with each lot of microcircuits delivered to this drawing.
- 3.8 <u>Notification of change for device class M.</u> For device class M, notification to DSCC-VA of change of product (see 6.2 herein) involving devices acquired to this drawing is required for any change as defined in MIL-STD-973.
- 3.9 <u>Verification and review for device class M.</u> For device class M, DSCC, DSCC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.
- 3.10 <u>Microcircuit group assignment for device class M</u>. Device class M devices covered by this drawing shall be in microcircuit group number 42 (see MIL-PRF-38535, appendix A).

4. QUALITY ASSURANCE PROVISIONS

- 4.1 <u>Sampling and inspection</u>. For device classes N, Q, and V, sampling and inspection procedures shall be in accordance with MIL-PRF-38535 or as modified in the device manufacturer's Quality Management (QM) plan. The modification in the QM plan shall not affect the form, fit, or function as described herein. For device class M, sampling and inspection procedures shall be in accordance with MIL-PRF-38535, appendix A.
- 4.2 <u>Screening</u>. For device classes N, Q, and V, screening shall be in accordance with MIL-PRF-38535, and shall be conducted on all devices prior to qualification and technology conformance inspection. For device class M, screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection.

4.2.1 Additional criteria for device class M.

- a. Delete the sequence specified as initial (preburn-in) electrical parameters through interim (postburn-in) electrical parameters of method 5004 and substitute lines 1 through 6 of table IIA herein.
- b. For device class M, the test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. For device class M, the test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015.
- c. Interim and final electrical parameters shall be as specified in table IIA herein.

4.2.2 Additional criteria for device classes N, Q, and V.

- a. The burn-in test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The burn-in test circuit shall be maintained under document revision level control of the device manufacturer's Technology Review Board (TRB) in accordance with MIL-PRF-38535 and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1015 of MIL-STD-883.
- b. Interim and final electrical test parameters shall be as specified in table IIA herein.
- Additional screening for device class V beyond the requirements of device class Q shall be as specified in appendix B of MIL-PRF-38535.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 5

		T.	ABLE I. <u>Electrical performance c</u>	characteristics.				
Test		Symbol	Conditions 3.0#Vcc#3.6V (-55EC#T _C #+125EC for	Group A Subgroups	Device Types			Units
			ceramic packages) (-55EC#T _J #+125EC for plastic packages)			Min	Max	
High-level output v	/oltage	VOH	IOH = -4 mA, VCC=min (LVTTL)	1, 2, 3	01	2.4		V
High-level output v	/oltage		IOH = -500 FA, VCC= min (LVCMOS)	1, 2, 3	01	90% VCC		V
Low-level output voltage		VOL	IOL = 12 mA, VCC=min (LVTTL) <u>1</u> /	1, 2, 3	01		0.4	V
Low-level output voltage			IOL = 1500 FA, VCC=min (LVCMOS)	1, 2, 3	01		10% VCC	V
Data Retention Supply Voltage (below which configuration data may be lost)		VDR	(Read back mode only)	1, 2, 3	01	2.5		V
Quiescent FPGA S current <u>2</u> /	Supply	ICCO		1, 2, 3	01		10	mA
Input or output lea	ıkage	IL		1, 2, 3	01	-10	+10	FA
Input capacitance (sample tested)	U and T case outlines	C _{IN} , C _{OUT}	See 4.4.1e, f = 1.0 Mhz, V _{OUT} = 0 V	4	01		10	pf
	X, Y, Z, case outlines						16	pf
Pad pull-up (wher	n selected)	IRPU	VIN = 0V (sample tested)	1, 2, 3	01	0.02	0.25	mA
Pad pull-down (w selected)	hen	IRPD	VIN = 3.6V (sample tested)	1, 2, 3	01	0.02	0.15	mA
Horizontal Longlin (when selected) @		IRLL		1, 2, 3	01	0.3	2.0	mA
Functional test		FT	See 4.4.1c	7, 8A, 8B	01			

See notes at end of table.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 6

TABLE I. Electrical performance characteristics.									
Test	Symbol	Condition 3.0#Vcc#3 (-55EC#T _C #+1 ceramic pack (-55EC#T _J #+1 plastic pack	3.6V 125EC for kages)	/	oup A Iroups	Device Types	Lir Min	mits Max	Units
Wide Decoder Switching Chara	Lacteristic Guideli		ages)						
Full length, two pull-ups,	TWAF2	See figure 4 as a	annlicable						
inputs from IOB I-pins 3/	1117112	4/ <u>5</u> /	арріїодоїо	9, 10	0, 11	01		9.1	ns
Half length, two pull-ups, inputs from IOB I-pins <u>3</u> /	TWAO2] - 3 = 3						6.5	
CLB Switching Characteristic Guidelines									
Combinatorial Delays									
F/G inputs to X/Y outputs	TILO	See figures 3 an	nd 4 as	9, 10,	, 11	01		1.6	ns
F/G inputs via H' to X/Y outputs	TIHO	applicable <u>4</u> / <u>5</u> /						2.7	
F/G inputs via transparent latch to Q outputs	ТІТО	See figures 3 and 4 as applicable <u>6</u> /						2.9	
C inputs via SR/HO via H to X/Y outputs	THH0O	See figures 3 and 4 as applicable 4/5/						2.5	
C inputs via HI via H to X/Y outputs	THH10]						2.4	
C inputs via DIN/H2 via H to X/Y outputs	THH2O]						2.5	
C inputs via EC, DIN/H2 to YQ, XQ output (bypass)	TCBYP	1						1.5	
CLB Fast Carry Logic		•				•	•		
Operand inputs (F1, F2, G1, G4) to COUT	TOPCY	See figure 3 as a <u>6</u> /	applicable	9, 10,	, 11	01		2.7	ns
Add/Subtract input (F3) to COUT	TASCY	See figure 3 as a <u>6</u> /	applicable					3.3	
Initialization inputs (F1,F3) to COUT	TINCY	See figure 3 as applicable 4/5/	/					2.0	
CIN through function generators to X/Y outputs	TSUM	See figure 3 as a <u>4</u> / <u>5</u> /	applicable					2.8	
CIN to COUT, bypass function generators	ТВҮР	See figure 3 as a <u>6</u> /	applicable					0.3	
Sequential Delays									
Clock K to Flip-Flop outputs Q	тско	See figures 3 and 4 as applicable 4/5/		9, 10,	11	01		2.1	ns
Clock K to Latch outputs Q	TCKLO	See figure 3	<u>6</u> /					2.1	
See notes at end of table.									
STANDARD MICROCIRCUIT DRAWING			SIZE A	:				5962-9	8513
DEFENSE SUPPLY (COLUMBUS, O			REVIS	SION LEVE	iL .	SHEET 7			

Test	Symbol	Conditions 3.0#Vcc#3.6\ (-55EC#T _C #+125I	SEC for	Group A Subgroups	Device Types	Li	mits	Units
		ceramic packag (-55EC#T _J #+125E plastic package	ges) EC for			Min	Max	
Setup Time before Clock K								
F/G inputs	TICK	See figure 3 6/		9, 10, 11	01	1.1		ns
F/G inputs via H	TIHCK					2.2		ns
C inputs via H0 through H	THH0CK					2		ns
C inputs via H1 through H	THH1CK					1.9		ns
C inputs via H2 through H	THH2CK					2		ns
C inputs Via DIN	TDICK					0.9		ns
C inputs via EC	TECCK					1		ns
C inputs via S/R, going Low (inactive)	TRCK					0.6		ns
CIN input via F/G	TCCK					2.3		ns
CIN input via F/G and H	TCHCK					3.4		ns
Hold Time after Clock K								
F/G inputs	TCKI	See figure 3	<u>6</u> /	9, 10, 11	01	0		ns
F/G inputs via H	TCKIH					0		ns
C inputs via SR/HO through H	TCKHH0					0		ns
C inputs via H1 through H	TCKHH1					0		ns
C inputs via DIN/H2 through H	TCKHH2					0		ns
C inputs via DIN/H2	TCKDI					0		ns
C inputs via EC	TCKEC					0		ns
C inputs via SR, going Low (inactive)	TCKR					0		ns

See notes at end of table.

STANDARD
MICROCIRCUIT DRAWING
DEFENSE SUPPLY CENTER COLUMBUS
COLUMBUS, OHIO 42316-5000

SIZE

A

SPECISION LEVEL
SHEET
8

Test	TABL Symbol	E I. Electrical peri		naracteris Grou		evice	Lii	mits	Units
	2,	3.0#Vcc#3 (-55EC#T _C #+1 ceramic pack (-55EC#T _J #+1 plastic pack	3.6V 125EC for kages) 125EC for	A Subgro	· Ty	ypes	Min	Max	
Clock		plastic pack	ages)						
Clock High time	тсн	See figure 3	<u>6</u> /	9, 10, 1	1 01	1	3		ns
Clock Low time	TCL						3		ns
Set/Reset Direct	•	•						•	
Width (High)	TRPW	See figure 3	<u>6</u> /	9, 10, 1	1 01	1	3		ns
Delay from C inputs via S/R, going High to Q	TRIO							3.7	ns
Global Set/Reset									
Minimum GSR Pulse Width	TMRW	See figure 3	<u>6</u> /	9, 10, 1	1 01	1	19.8		ns
Delay from GSR input to any Q	TMRQ							15.9	ns
Delay from GSR input to any Pad	TRPO							20.5	ns
Toggle Frequency (MHz)	FTOG							166	MHz
Propogation Delays									
Clock (OK) to Pad	TOKPOF	See figure 3	<u>6</u> /	9, 10, 1	1 01	1		5	ns
Output (O) to Pad	TOPF							4.1	
3 state to Pad hi-Z (slew-rate independent)	TTSHZ							4.4	
3-state to Pad active and valid	TTSONF							4.1	
Output (O) to Pad via Fast Output MUX	TOFPF							5.5	
Setup and Hold Times									
Output (O) to clock (OK) setup time	TOOK	See figure 3	<u>6</u> / <u>8</u> /	9, 10, 1	1 01	1	0.5		
Output (O) to clock (OK) hold time	TOKO						0		
Clock Enable (EC) to clock (OK) setup	TECOK						0		
Clock Enable (EC) to clock (OK) hold	TOKEC						0.3		
See notes at end of table.									
	DARD JIT DRAWING		SIZE A					5962-	98513
DEFENSE SUPPLY (COLUMBUS, O	CENTER COLU			F	REVISION	N LEVE	L	SHEET)

	TABL	E I. <u>Electrical perf</u>	ormance ch	naracter	istics.				
Test	Symbol	Condition 3.0#Vcc#3 (-55EC#T _C #+1 ceramic pack (-55EC#T _J #+1 plastic pack	3.6V 25EC for kages)	Gro A Subg	oup \ roups	Device Types	Lir Min	mits Max	Units
		plastic pack	ages)						
Slew Rate Adjustment	1	I					1	1	<u> </u>
for output SLOW option add	TSLOW	<u>6</u> /		9, 10	11	01		3	ns
BENCHMARK PATTERNS (10	00% Tested) Co	onditions				1	T	1	
Core + TILO+TIHO	TILHO1	See figure 4 as a 4/ 5/ 9/	applicable	9, 10,	11	01		51.7	ns
Core + TILO+TIHO	TILHO2	<u> </u>						51.8	
Core + TILO+TIHO	TILHO3							52	
Core + TILO+TIHO	TILHO4							51.9	
Core + TILO+TIHO	TILHO5							52.9	
Core + THH0O +THECQO	THH0O							82.3	
Core + THH10 + THH2QO	THH10							85.7	
Core + THH20 + THELQO	THH20							81.6	
Core + TINCY + TSUM	CRY1	1						68.4	
Local Line Patterns									
Core + Local Line 1	LOCAL 1	See figure 4 as a	applicable	9, 10,	11	01		93.6	ns
Core + Local Line 2	LOCAL 2	<u>4</u> / <u>5</u> / <u>9</u> /						102.9	
Core + Local Line 3	LOCAL 3	1						105.2	
Core + Local Line 4	LOCAL 4	1						107.3	
Core + Local Line 5	LOCAL 5							124.3	
Core + Local Line 6	LOCAL 6							115.8	
Core + Local Line 7	LOCAL 7							102.5	
Core + Local Line 8	LOCAL 8							97.7	
Core + Local Double Line 1	DBL 1							84.5	
Core + Local Double Line 2	DBL 2							86	
Core + Horizontal Quad A	QHA							131.9	
Core + Horizontal Quad B	QHB	1						140.7	
Core + Horizontal Quad C	QHC	1						138.2	
Core + Verticle Quad A	QVA	1						136.8	
Core + Verticle Quad B	QVB	1						139.2	
Core + Verticle Quad C	QVC	1						137	
See notes at end of table.									
MICROCIRCU	DARD JIT DRAWING		SIZE A					5962-9	8513
DEFENSE SUPPLY (COLUMBUS, O					REVIS	ION LEVE	EL	SHEET 10)

	TABL	E I. Electrical perf	ormance ch	naracter	ristics.				
Test	Symbol	Conditio 3.0#Vcc#3 (-55EC#T _C #+1 ceramic pacl	3.6V 25EC for	1	oup A roups	Device Types		nits	Units
		(-55EC#T _J #+1 plastic pack	25EC for				Min	Max	
Long-Line patterns									
Core + Horizontal Long Line 1	HLL1	See figure 4 as	applicable	9, 10,	11	01		74.9	ns
Core + Horizontal Long Line 2	HLL2	<u>4</u> / <u>5</u> / <u>9</u> /						119.2	
Core + Horizontal Long Line 3	HLL3							93.4	
Core + Horizontal Long Line 4	HLL4							76.5	
Core + Horizontal Long Line 5	HLL5							111.2	
Core + Horizontal Long Line 6	HLL6							108.2	
Core + Vertical Long Line 1	VLL1							58.8	
Core + Vertical Long Line 2	VLL2							59.5	
Core + Vertical Long Line 3	VLL3							62.1	
Core + Vertical Long Line 4	VLL4							62.6	
Core + Vertical Long Line 5	VLL5							60	
Core + Vertical Long Line 6	VLL6							60.8	
Core + Vertical Long Line 7	VLL7							63.1	
Core + Vertical Long Line 8	VLL8							62.4	
Core + Vertical Long Line 9	VLL9							63.4	
Core + Vertical Long Line 10	VLL10							61.4	
Core + Horizontal Long Line 1 (Loaded)	HLL1_L]						105.5	
Core + Horizontal Long Line 2 (Loaded)	HLL2_L							163.2	
Core + Horizontal Long Line 3 (Loaded)	HLL3_L							131.3	
Core + Horizontal Long Line 4 (Loaded)	HLL4_L							106	
Core + Horizontal Long Line 5 (Loaded)	HLL5_L							151.6	
Core + Horizontal Long Line 6 (Loaded)	HLL6_L							154.9	
See notes at end of table.									
	STANDARD MICROCIRCUIT DRAWING		SIZE A					5962-9	8513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000					REVIS	ION LEVE	L	SHEET 1 1	l

	TABL	_E I. <u>Electrical perf</u>	ormance ch	naracteri	istics.				
Test	Symbol	Condition 3.0#Vcc#3 (-55EC#T _{.C} #+1.	.6V 25EC for	Gro A Subgr	٠	Device Types	Lin	nits	Units
		ceramic pack (-55EC#T _J #+12 plastic packa	25EC for				Min	Max	
Core + Vertical Long Line 1 (Loaded)	VLL1_L	See figure 4 as a 4/ 5/ 9/	pplicable	9, 10,	11	01		80.9	ns
Core + Vertical Long Line 2 (Loaded)	VLL2_L							75.5	
Core + Vertical Long Line 3 (Loaded)	VLL3_L							77.3	
Core + Vertical Long Line 4 (Loaded)	VLL4_L							80.3	
Core + Vertical Long Line 5 (Loaded)	VLL5_L							74.8	
Core + Vertical Long Line 6 (Loaded)	VLL6_L							78.1	
Core + Vertical Long Line 7 (Loaded)	VLL7_L							79.4	
Core + Vertical Long Line 8 (Loaded)	VLL8_L							80	
Core + Vertical Long Line 9 (Loaded)	VLL9_L							70.7	
Core + Vertical Long Line 10 (Loaded)	VLL10_L							77	
Clock Patterns									
Global Low Skew Clock	GLS	See figure 4 as a	pplicable	9, 10,	11	01		53.1	ns
Global Early Clock	GE	<u>4</u> / <u>5</u> /						112.1	
KX Clock Line	KX_K							113.7	
Edge Line Patterns									
Core + Edge Long Line	EDGELL	See figure 4 as a		9, 10,	11	01		117.4	ns
Octal 1	OCTAL 1	<u>4</u> / <u>5</u> / and <u>(9</u> / wl applicable)	nere					60.4	
Core + Top Edge Double Line	T_EDBL							44.7	
Core + Left Edge Double Line	L_EDBL							40.2	
Core + Bottom Edge Double Line	B_EDBL							42.8	
See notes at end of table.									
	DARD JIT DRAWING		SIZE A					5962-9	8513
DEFENSE SUPPLY	MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000				REVIS	ION LEVE	L	SHEET 12	2

	TABI	_E I. <u>Electrical perf</u>	ormance ch	haracte	ristics.				
Test	Symbol	Conditior 3.0#Vcc#3 (-55EC#T _C #+1	.6V 25EC for	/	oup A roups	Device Types	Lir	nits	Units
		ceramič pack (-55EC#T _J #+12 plastic packa	25EC for				Min	Max	
Core +Right Edge Double Line	R_EDBL	See figure 4 as a <u>4</u> / <u>5</u> / and (<u>9</u> / applicable	where	9, 10,	11	01		41.6	ns
Top Left Half Wide Decoder	TL_HWD2	арріісаріі	e)					39.6	
Top Right Half Wide Decoder	TR_HWD2							66.7	
Full Wide Decoder	R_WD2							53	
Buffer Patterns									
Full Length Tbuf at HLL3	F_TBUF3			0.40	4.4	0.4		94.1	
Full Length Tbuf at HLL4	F_TBUF4	See figure 4 as a _l <u>4</u> / <u>5</u> /	pplicable	9, 10,	11	01		84.7	ns
Left Half Length Tbuf at HLL3 with 4 Pullup	L_TBUF3_4							65.8	
Left Half Length Tbuf at HLL4 with 4 Pullup	L_TBUF4_4							62.5	
Left Half Length Tbuf at HLL3 with 1 Pullup	L_TBUF3_1							115.8	
Left Half Length Tbuf at HLL4 with 1 Pullup	L_TBUF4_1							107.3	
Right Half Length Tbuf at HLL3 with 4 Pullup	R_TBUF3_4							67.2	
Right Half Length Tbuf at HLL4 with 4 Pullup	R_TBUF4_4							62.5	
Right Half Length Tbuf at HLL3 with 1 Pullup	R_TBUF3_1							115.6	
Right Half Length Tbuf at HLL4 with 1 Pullup	R_TBUF4_1							107.7	
Clock/Setup/Hold Patterns									
GLS Clock Setup	SETUP_GLS	See figure 4 as a	pplicable	9, 10,	11	01	6.4		ns
GE Clock Setup	SETUP_GE	<u>4</u> / <u>5</u> /					6.4		
GLS Clock Hold	HOLD_GLS						0		
GE Clock Hold	HOLD_GE						0]
GE Clock Hold	TCKO_GLS_ POS							8.5	
See notes at end of table.									
	ANDARD		SIZE A					5962-9	98513
DEFENSE SUPPLY	MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000				REVIS	SION LEVE	iL	SHEET 1;	3

	TABLE I. <u>E</u>	lectrical perf	ormance charac	cteristics.				
Test	Symbol	3.0#\ (-55EC#T _c ceramic (-55EC#T	nditions Vcc#3.6V 2 #+125EC for packages) J #+125EC for packages)	Group A Subgroups	Device Types	Lir Min	Max	Units
GLS Clock To Out (rise)	TCKO_GLS_NEG	See figure		9, 10, 11	01		8.5	ns
GLS Clock To Out (fall)	TCKO_GE_POS	applicable	<u>4</u> / <u>5</u> /				8.5	
GE Clock To Out (fall)	TCKO_GE_NEG						8.5	
IOB Patterns (CMOS)								
TPPLI To TOPS	TPPLI_TOPS	See figure		9, 10, 11	01		16.7	ns
TPID To Out Thru MUX1	TPID_TMUX1		<u>4</u> / <u>5</u> / and e applicable)				7.3	
TPID to TOPF Thru Wide Decoder	TPID_WDEC_TOPF						17.9	
TPLI To Out Thru EC	TPLI_TECI						9.1	
TPPLI To Out Thru EC	TPPLI_TEC						15.1	
TPDLI To TOPF	TPDLI_TOPF						16.6	
TPFLI to TOPF	TPFLI_TOPF						9.2	
TPID To Out Thru MUX0	TPID_TMUXO						7.9	
TPPFLI To TOPF	TPPFLI_TOPF						14.3	
TPID To TOPF	TPID_TOPF						5.8	
TBUF driving half a Horizonta	al Longline (Horizontal L	ongline Swit	ching Character	istics Guideline	es)			
I going High or Low to half of a Horizontal Longline going High or Low, while T is Low. Buffer is constantly active.	T HIO1	See figure applicable	4 as 4/ <u>5</u> / <u>11</u> /	9, 10, 11	01		3.8	ns
T going Low to half of a Horizontal Longline going from resistive pull-up or floating High to active Low. TBUF configured as open- drain or active buffer with I = Low	THON						4.5	
T going High to half of a Horizontal Longline going from Low to High, pulled up by four resistors. 12/	T HPU4						4.3	
See notes at end of table.								
_	NDARD CUIT DRAWING		SIZE A				5962-9	8513
MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		S		REVISION	LEVEL	SI	HEET 1 4	1

	TABLE I.	Electrical perf	ormance char	acteristic	CS.				
Test	Symbol	Condi 3.0#Vc (-55EC#T _C # ceramic p	c#3.6V	Gro A Subgro	-	Device Types	Liı	mits	Units
		ceramic p (-55EC#T _J # plastic pa	+125EC for				Min	Max	
TBUF driving a Horizontal Lo	ongline								
I going High or Low to Horizontal Longline going High or Low, while T is Low. Buffer is constantly active.	T IOI	See figure 4 applicable 4		9, 10,	11	01		7.7	ns
T going Low to Horizontal Longline going from resistive pull-up or floating High to active Low. TBUF configured as open-drain or active buffer with I = Low.	TON							8.4	
T going High to Horizontal Longline going from Low to High, pulled up by two resistors. 13/	T PU2							7.9	
Setup Times (IOB Input Swit	ching Characteristic G	Guidelines)							
Pad to Clock (IK), no delay	TPICK	See figure 3		9, 10,	11	01	1.7		ns
Pad to Clock (IK), partial delay	TPICKP	applicable <u>6</u>	<u>5/</u>				7.8		
Pad to Clock (IK), full delay	TPICKD						9.7		
Pad to Clock (IK), via transparent Fast Capture Latch, no delay	TPICKF						2.4		
Pad to Clock (IK), via transparent Fast Capture Latch, partial delay	TPICKFP						8.4		
Pad to Fast Capture Latch Enable (OK), no delay	TPOCK <u>8</u> /						0.7		
Clock Enable (EC) to Clock (IK)	TECIK <u>8</u> /						0.3		
Hold Times			,				ı		1
All Hold times	<u>8</u> /	See figure 3 applicable 6		9, 10 ,	11	01	0		ns
See notes at end of table.									
	STANDARD MICROCIRCUIT DRAWING							5962-9	8513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000			RE	EVISIO	N LEVEL		SHEET 1	5	

Test	Symbol	Conditions 3.0#Vcc#3.6V (-55EC#T _C #+125EC for	Group A Subgroups	Device Types	Li	mits	Units
		ceramic packages) (-55EC#T _J #+125EC for plastic packages)	Cubgroups		Min	Max	
Propagation Delays							
Pad to I1, 12 via transparent FCL and input latch, no delay <u>14</u> /	TPFLI	See figures 3 and 4 as applicable 4/5/	9, 10, 11	01		3.1	ns
Pad to I1, 12 via transparent FCL and input latch, partial delay 14/	TPPFLI					9.2	
Clock (IK) to I1, 12 (flip flop)	TIKRI	See figures 3 and 4 as applicable 6/				1.8	
Clock (IK) to I1, 12 (latch enable, active Low)	TIKLI					1.9	
FCL Enable (OK) active edge to I1, 12 (via transparent standard input latch) 14/	TOKLI					3.6	
Minimum GSR Pulse Width	TMRW				19.8		
Delay from GSR input to any Q	TRRI					15.9	
Delay from FCL enable (OK) active edge to IFF clock (IK) active edge 15/	TOKIK				1.7		
Pad to I1, 12	TPID	See figures 3 and 4 as				1.6	
Pad to I1, 12 via transparent latch, no delay	TPLI	applicable <u>4</u> / <u>5</u> /				2.6	
Pad to I1, 12 via transparent input latch, partial delay	TPPLI					9.2	
Pad to I1, 12 via transparent input latch, full delay	TPDLI					11.0	

STANDARD
MICROCIRCUIT DRAWING
DEFENSE SUPPLY CENTER COLUMBUS
COLUMBUS, OHIO 42316-5000

SIZE

A

SP62-98513

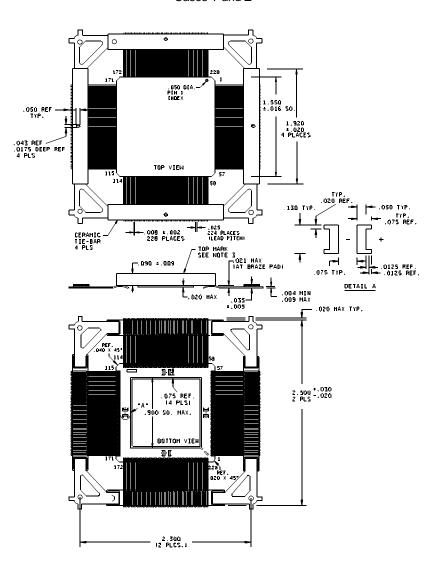
REVISION LEVEL
SHEET
16

	TABLE I.	Electrical perf	ormance char	racteri	istics.				
Test	Symbol	Condi 3.0#Vcc (-55EC#T _C #	c#3.6V #+125EC for		Group A ogroups	Device Types	Li	imits	Units
		ceramic packages) (-55EC#T J #+125EC for plastic packages)					Min	Max	
Output Flip-Flop, Clock to O	ut (Pin to Pin Output p	arametrics Gui	idelines)						
Global Low Skew Clock to Output using OFF <u>16</u> /	TICKOF	See figures 3 applicable		9, 1	0, 11	01		8.6	ns
Global Early Clock to Output using OFF Values are for BUFGE #s 1, 2, 5 and 6. Add 1.4 ns for BUFGE #s 3, 4, 7 and 8 16/ 18/	TICKEOF							7.4	
For output SLOW option add	TSLOW							3.0	
Output/Output Mux/Clock to	out								
Global Low Skew Clock to Output using OMUX 19/	TPFPF	See figure 3 applicable 6		9, 1	0, 11	01		8.8	ns
Global Early Clock to Output using OMUX Values are for BUFGE #s 1, 2, 5 and 6. Add 1.4 ns for BUFGE #s 3, 4, 7 and 8 18/ 19/	TPEFPF							7.6	
For output SLOW option add	TSLOW							3.0	
Global Low Skew Clock, Set	-Up and Hold								
Input Setup Time, using Global Low Skew clock and IFF (full delay) 15/	TPSD	See figure 3 applicable 6		9, 1	0, 11	01	6.4		ns
Input Hold Time, using Global Low Skew clock and IFF (full delay) <u>15</u> /	TPHD						0		
Global Buffers Switching Cha	aracteristic Guidelines								
From pad through Global Low Skew buffer, to any clock K	TGLS	See figure 4 applicable 4		9, 1	0, 11	01		3.6	ns
From pad through Global Early buffer, to any clock K in same quadrant	TGE							2.4	
See notes at end of table.									
_	STANDARD MICROCIPCIUT DRAWING							5962-9	98513
MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000					REVISIO	N LEVEL		SHEET 1	7

- 1/ With up to 64 pins simultaneously sinking 12 mA.
- 2/ With no output current loads, no active input or Longline pull-up resistors, all I/O pins tri-stated and floating.
- 3/ These delays are specified from the decoder input to the decoder output. Fewer than the specified number of pull up resistors can be used, if desired. Using fewer pull ups reduces power consumption but increases delays. Use the static timing analyzer to determine delays if fewer pull ups are used.
- 4/ Parameter is not directly tested. Devices are first 100 percent functionally tested. Benchmark timing patterns are then used to determine the compliance of this parameter. Characterization data is taken at initial device introduction, and after any design or process changes which may affect this parameter.
- 5/ Benchmark patterns are used to determine compliance to this parameter.
- 6/ Parameter is not tested but is guaranteed by design through simulation.
- 7/ Maximum flip-flop toggle rate for export control purposes.
- 8/ Input pad setup times and hold times are specified with respect to the internal clock (IK). To calculate setup time, Subtract clock delay (clock pad to IK) from the specified input pad setup time value, but do not subtract below zero, "Negative" hold time means that the delay in the input data is adequate for the external system hold time to be zero, provided the input clock uses the global signal distribution from pad to IK.
- 9/ Core = TILO + TCKO
- 10/ These delays are specified from the decoder input to the decoder outure. For pad-to-pad delays, add the input delay (TPID) output delay (TOPF or TOPS).
- 11/ These values include a minimum load of one output, spaced a far as possible from the active pullup(s). Use the static timing analyzer to determine the delay for each destination.
- 12/ Fewer than the specified number of pullup resistors can be used, if desired. Using fewer pullups reduces the power consumption but increases delays. Use the static analyzer to determine delays if fewer pullups are used.
- 13/ These values are for a minimum load with the driver paced as far as possible from the active pull up(s). Fewer than the specified number of pull up resistors can be used, if desired. Using fewer pull ups reduces power consumption but increases delays. Use the static timing analyzer to determine delays if fewer pull ups are used.
- 14/ FCL = Fast Capture Latch
- 15/ IFF = Input Flip-Flop or Latch
- 16/ OFF = Output Flip Flop
- 17/ These are representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible IOB and CLB flip-flops are clocked by the global clock net. Output timing is measured at ~50% VCC threshold with 35 pF external capacitive load.
- 18/ BUFGE = Global Early Buffers
- 19/ OMUX = Output MUX
- 20/ Setup time is measured with the fastest route and the lightest load. Use the static timing analyzer to determine the setup time under given design conditions. Hold time is measured using the furthest distance and a reference load of one clock pin per two IOBs. Use the static timing analyzer to determine the setup and hold time under given design conditions.
- 21/ Parameters are for BUFGE # 1, 2, 5 and 6. Add 1.4 ns for BUFGE # 3, 4, 7 and 8.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 18

Cases Y and Z



NOTES:

- 1. Dimensions are in inches.
- Packages are shipped flat as depicted
- Lead dimensions call out includes lead finish.

 The leads of this package style shall be protected from mechanical distortion and damage such that dimensions pertaining to relative lead/body "true positions" and lead "coplanarity" are always maintained until the next higher level package attachment process is complete. Package lead protection mechanisms (tie bars) are shown on the drawing for reference only. When microcircuit devices contained in this package style are shipped for use in Government equipment, or shipped directly to the Government as spare parts or mechanical qualification samples, lead "true position" and "coplanarity" protection shall be in
- place.
 Case Y represents marking the device on the nonlid side of device, i.e., lid side facing down. When mounted in this position, the pin out is clockwise. Case Z represents marking the device on the lid side of the device i.e., lid side facing up. When mounted in this position, the pin out is counterclockwise.

FIGURE 1. Case outline.

SIZE 5962-98513 **STANDARD** Α MICROCIRCUIT DRAWING **DEFENSE SUPPLY CENTER COLUMBUS** REVISION LEVEL SHEET **COLUMBUS, OHIO 42316-5000** 19

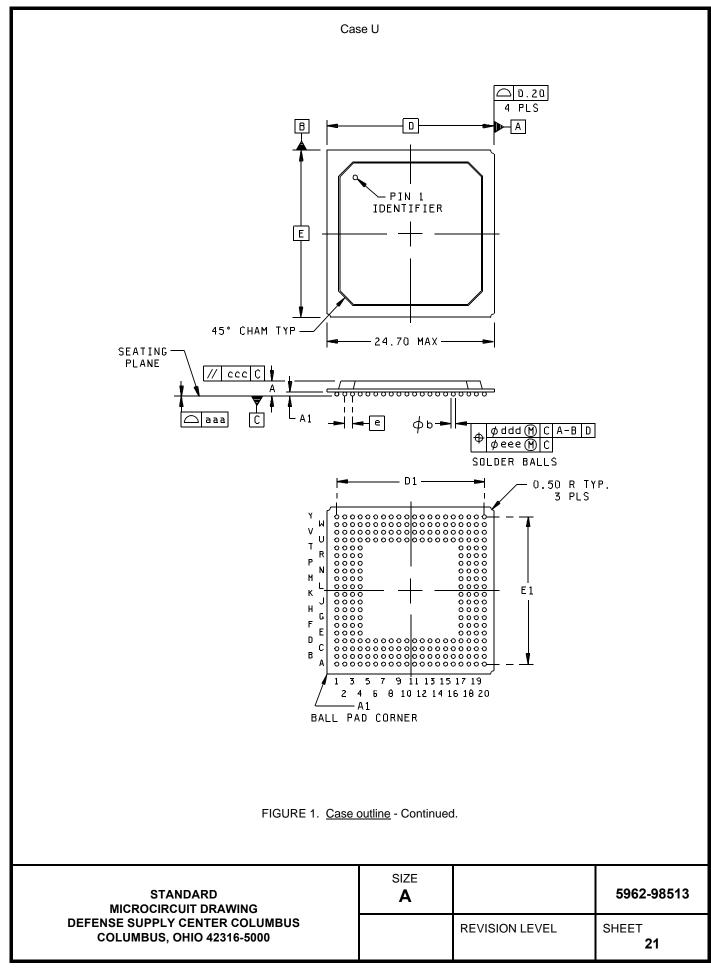
Cases Y and Z - Continued

Inch to metric conversion table for convenience only.

Inches	Metric mm
2.500 2.300 1.920 1.550 .900 .130 .125 .090 .075 .050 .043 .040 .035 .030 .025 .021 .020 .0175 .016 .0125 .009 .008	63.50 58.42 48.77 39.37 22.86 3.30 3.18 2.29 1.91 1.27 1.09 1.02 .89 .76 .64 .53 .51 .44 .41 .32 .23 .20
.005 .004 .002	.13 .10 .05

FIGURE 1. <u>Case outline</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 20



Case U - Continued.

BG256						
Symbol		Millimeters				
	Min.	Nom.	Max.			
Α		2.33	3.50			
A1	0.50	0.60	0.70			
D/E		27.00 BSC				
D1/E1	24.14 REF					
е	1.27 BSC					
i b	0.60	0.75	0.90			
aaa			0.20			
ccc			0.35			
ddd			0.30			
eee	0.15					
М	20					
REF	JEDE	EC MO-151-BAL	2			

Notes:

- All dimensions and tolerances conform to ANSI Y14.5M-1994.
 Symbol "M" is the pin matrix size.
 Conforms to JEDEC MO-192 (Depopulated).

FIGURE 1. <u>Case outline</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 22

Device type	All	Device type	All	Device type	All
Case outline	Х	Case outline	Х	Case outline	Х
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
A2	TDI_I/O	C11	I/O	G18	I/O
A3	I/O	C12	GND	H1	A18_I/O
A4	I/O_FCLK1	C13	I/O	H2	I/O
A5	I/O	C14	I/O	H3	I/O
A6	I/O	C15	M1	H4	I/O
A7	I/O	C16	M2	H15	I/O
A8	I/O	C17	I/O	H16	I/O
A9	I/O	C18	I/O	H17	I/O
A10	I/O	D1	I/O	H18	I/O
A11	I/O	D2	A13_I/O	J1	A19_I/O
A11	I/O I/O	D2	VCC	J2	A19_1/O A9_1/O
A12 A13	I/O_FCLK2	D3 D4	GND	J2 J3	A9_I/O A8_I/O
A14	I/O	D5	I/O	J4	VCC
A15	I/O	D6	I/O	J15	VCC
A16	I/O	D7	I/O	J16	& BI & &_ I/O
A17	I/O	D8	1/0	J17	I/O
A18	MO	D9	GND	J18	I/O
B1	I/O	D10	VCC	K1	A20_I/O
B2	BUFGS_TL_GCK8	D11	I/O	K2	A6_I/O
	_A15_I/O	D12	I/O	K3	A7_I/O
B3	I/O	D13	I/O	K4	GND
B4	TCK_I/O	D14	I/O	K15	GND
B5	I/O	D15	GND	K16	I/O
B6	I/O	D16	VCC	K17	I/O
B7	TMS_I/O	D17	I/O	K18	I/O
B8	I/O	D18	I/O	L1	A21_I/O
B9	I/O	E1	I/O	L2	I/O
B10	I/O	E2	I/O	L3	I/O
B11	I/O	E3	I/O	L4	I/O
B12	I/O	E4	I/O	L15	I/O
B13	I/O	E15	I/O	L16	I/O
B14	I/O	E16	HDC_I/O	L17	I/O
B15	I/O	E17	&&&_I/O	L18	I/O
B16	BUFGS_BL_	E18	I/O	M1	A5_I/O
-	GCK2_I/O	F1	I/O	M2	A4_I/O
B17	BUFGP_BL_	F2	I/O	M3	GND
	GCK3_I/O	F3	A12_I/O	M4	1/0
B18	1/0	F4	1/O	M15	I/O
C1	I/O	F15	I/O	M16	GND
C2	A14_I/O	F16	I/O	M17	1/0
C3	BUFGP_TL_A16_	F17	I/O	M18	I/O
55	GCK1_I/O	F18	I/O	N1	1/O 1/O
C4	A17_I/O	G1	A10_I/O	N2	I/O
C5	A17_1/O 1/O	G2		N2 N3	
			A11_I/O		A3_I/O
C6	I/O	G3	GND	N4	I/O
C7	GND	G4	I/O	N15	I/O
C8	I/O	G15	I/O CND	N16	I/O
C9 C10	I/O	G16	GND VO	N17	I/O
CTU	I/O	G17	I/O	N18	I/O

FIGURE 2. <u>Terminal connections</u>.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 23

Device type	All	Device type	All	Device type	All
Case outline	Х	Case outline	Х	Case outline	Х
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
P1 P2 P3 P4 P15 P16 P17 P18 R1 R2 R3 R4 R5 R6 R7 R8 R9 R10 R11 R12 R13 R14 R15 R16 R17 R18 T1 T2	I/O	T3 T4 T5 T6 T7 T8 T9 T10 T11 T12 T13 T14 T15 T16 T17 T18 U1 U2 U3 U4 U5 U6 U7 U8 U9	A0_W8_I/O BUFGS_TR_GCK6 _DOUT_I/O I/O I/O GND I/O J/O GND I/O J/O GND I/O J/O BUFGS_BR_ GCK4_I/O I/O J/O BUFGP_TR_GCK7 _A1_I/O TDO D0_DIN_I/O I/O I/O FCLK4 I/O I/O R8_I/O	U10 U11 U12 U13 U14 U15 U16 U17 U18 V1 V2 V3 V4 V5 V6 V7 V8 V9 V10 V11 V12 V13 V14 V15 V16 V17 V18	D4_I/O I/O D5_I/O I/O_FCLK3 I/O I/OBUFGP_BR_ GCK5_I/O DONE I/O CCLK RDY_BN&*_ RG&K_I/O D1_I/O I/O I/O I/O I/O I/O I/O I/O I/O I/O

FIGURE 2. <u>Terminal connections</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 24

Case	outlines	Υ	and	Ζ

Device type	All	Device type	All	Device type	All
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
1 2 3 4 5 6 7 8 9 10 11 2 13 14 5 6 7 8 9 10 11 2 13 14 5 6 17 8 19 20 1 22 23 24 25 26 27 28 29 30 31 32 33 34 35 36 37 38 39 40 41 42 43 44 45 46 47 48 49 50	VSS BUFGP_TL_A16_ GCK1_I/O A17_I/O I/O TDI_I/O I/O I/O I/O I/O I/O I/O I/O I/O I/O	51 52 53 54 55 56 57 58 60 61 62 63 64 65 66 67 77 77 77 77 77 77 77 77 77 77 77	I/O I/O I/O BUFGS_BL_GCK2_I/O M1 VSS M0 VCC M2 BUFGP_BL_GCK3_I/O HDC_I/O I/O I/O I/O I/O I/O I/O I/O I/O I/O	101 102 103 104 105 106 107 108 109 110 111 112 113 114 115 116 117 118 119 120 121 122 123 124 125 126 127 128 129 130 131 132 133 134 135 136 137 138 139 140 141 142 143 144 145 146 147 148 149 150	I/O

FIGURE 2. <u>Terminal connections</u>.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000	SIZE A		5962-98513
		REVISION LEVEL	SHEET 25

Case outlines Y and Z Continued.

Device type	All	Device type	All	Device type	All
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
151 152 153 154 155 156 157 158 159 160 161 162 163 164 165 166 167 168 169 170 171 172 173 174 175 176	I/O VCC I/O I/O_FCLK4 I/O I/O VSS I/O I/O I/O I/O I/O I/O I/O D1_I/O RDY_BNS%_RC&K_I/O I/O D0_DIN_I/O BUFGS_TR_GCK6_DOUT_I/O CCLK VCC TDO VSS A0_WS_I/O BUFGP_TR_GCK7_A1_I/O I/O	177 178 179 180 181 182 183 184 185 186 187 188 189 190 191 192 193 194 195 196 197 198 199 200 201 202	I/O CSI_A2_I/O A3_I/O I/O I/O I/O I/O I/O I/O I/O I/O I/O	203 204 205 206 207 208 209 210 211 212 213 214 215 216 217 218 219 220 221 222 223 224 225 226 227 228	A9_I/O A19_I/O A18_I/O I/O I/O I/O A10_I/O A11_I/O VCC I/O

FIGURE 2. <u>Terminal connections</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 26

Device type	All	Device type	All	Device type	All
Case outline	U	Case outline	U	Case outline	U
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
A1 A2 A3 A4 A5 A6 A7 A8 A9 A10 A11 A12 A13 A14 A15 A16 A17 A18 A19 A20 B1 B2 B3 B4 B5 B6 B7 B8 B10 B11 B12 B13 B14 B15 B16 B17 C1 C2 C3 C4 C5 C6 C7 C7 C8 C9 C10	GND A14_I/O A13_I/O I/O I/O I/O NO CONNECT A10_I/O A19_I/O A6_I/O A20_I/O I/O NO CONNECT I/O I/O NO CONNECT I/O I/O CSI_A2_I/O TDO CCLK BUFGP_TL_A16_ GCK1_I/O I/O A12_I/O I/O A12_I/O I/O A12_I/O I/O A12_I/O I/O BUFGP_TR_GCK7 A1_I/O A1_I/O A0_WS_I/O BUFGS_TR_GCK6 DOUT_I/O I/O TCK_I/O BUFGS_TL_GCK8_ A17_I/O	C11 C12 C13 C14 C15 C16 C17 C18 C19 C10 D1 D1 D1 D1 D1 D1 D1 D1 D1 D1 D1 D1 D1	A21_I/O	G20 H1 H2 H3 H4 H17 H18 H20 J1 J2 J3 J17 J18 J19 J20 K1 K2 K3 K4 K17 K18 K20 L1 L2 L3 L4 L17 L18 L20 M1 M20 M1 M20 N1 N1 N1 N1 N1 N1 N1 N1 N1 N1 N1 N1 N1	GND 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0 1/0

FIGURE 2. <u>Terminal connections</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 27

Device type	All	Device type	All	Device type	All
Case outline	U	Case outline	U	Case outline	U
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
P18 P19 P20 R1 R2 R3 R4 R17 R18 R19 R20 T1 T2 T3 T4 T17 T18 T19 T20 U1 U2 U3 U4 U5 U6 U7 U8 U9 U110 U112 U13 U14 U15	I/O VCC I/O VCC I/O VCC VCC I/O I/O I/O I/O I/O I/O I/O I/O I/O I/O	U16 U17 U18 U19 U20 V1 V2 V3 V4 V5 V6 V7 V8 V9 V10 V11 V12 V13 V14 V15 V16 V17 V18 V19 V20 W1 W2 W3 W4 W5 W6 W7	/O GND BUFGP_BR_ GCK5_ /O D7_ /O I/O I/O I/O I/O BUFGS_BL_ GCK2_ I/O I/O	W8 W9 W10 W11 W12 W13 W14 W15 W16 W17 W18 W19 W20 Y1 Y2 Y3 Y4 Y5 Y6 Y7 Y8 Y9 Y10 Y11 Y12 Y13 Y14 Y15 Y16 Y17 Y18 Y19 Y20	I/O NO CONNECT I/O &N&&

 $\label{eq:FIGURE 2.} \underline{\text{Terminal connections}} \text{ - Continued}.$

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 28

Device type	All	Device type	All	Device type	All
Case outline	Т	Case outline	Т	Case outline	Т
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
P1 P2 P3 P4 P5 P6 P7 P8 P9 P10 P11 P12 P13 P14 P15 P16 P17 P18 P19 P20 P21 P22 P23 P24 P25 P26 P27 P28 P29 P30 P31 P32 P33 P34 P35	VSS BUFGP_TL_A16 _GCK1_I/O A17_I/O I/O I/O TDI_I/O TCK_I/O I/O I/O I/O VSS I/O_FCLK1 I/O VCC I/O VCC I/O I/O VSS I/O	P36 P37 P38 P39 P40 P41 P42 P43 P44 P45 P46 P47 P48 P49 P50 P51 P52 P53 P554 P55 P56 P57 P58 P59 P60 P61 P62 P63 P64 P65 P67 P68 P69	/O VSS /O /O /O /O /O /O /O /O /O /O	P70 P71 P72 P73 P74 P75 P76 P77 P78 P79 P80 P81 P82 P83 P84 P85 P86 P87 P88 P89 P90 P91 P92 P93 P94 P95 P96 P97 P98 P99 P100 P101 P102 P103 P104 P105	\O\O\O\O\S\\\\\\\\\\\\\\\\\\\\\\\\\\\\

FIGURE 2. <u>Terminal connections</u> - Continued.

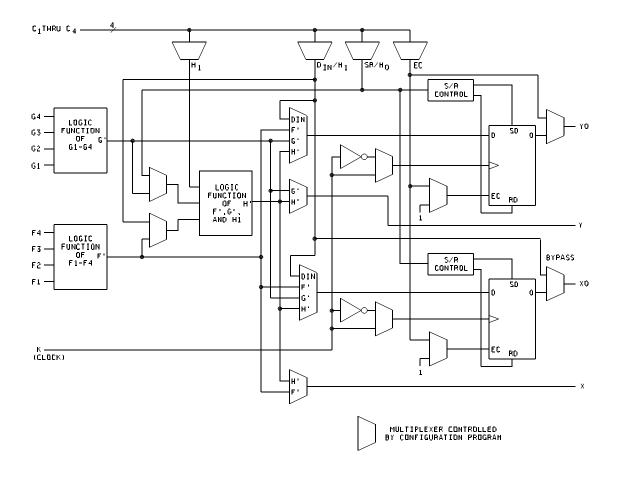
STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 29

Device type	All	Device type	All	Device type	All
Case outline	Т	Case outline	Т	Case outline	Т
Terminal number	Terminal symbol	Terminal number	Terminal symbol	Terminal number	Terminal symbol
P106 P107 P108 P109 P110 P111 P112 P113 P114 P115 P116 P117 P118 P119 P120 P121 P122 P123 P124 P125 P126 P127 P128 P129 P130 P131 P132 P133 P134 P135 P136 P137 P138 P139 P130 P131 P135 P136 P137 P138 P139 P140 P141 P142 P143 P144 P145 P146 P147 P148 P149 P150	VSS I/O	P151 P152 P153 P154 P155 P156 P157 P158 P159 P160 P161 P162 P163 P164 P165 P166 P167 P168 P170 P171 P172 P173 P174 P177 P178 P178 P179 P180 P181 P182 P183 P184 P185 P186 P187 P188 P189 P190 P191 P192 P193 P194	VSS D3_I/O R8_I/O I/O I/O I/O I/O I/O VSS D2_I/O I/O VCC I/O I/O_FCLK4 I/O I/O VSS I/O I/O I/O VSS I/O I/O I/O I/O SS I/O I/O I/O I/O I/O I/O SS I/O	P195 P196 P197 P198 P199 P200 P201 P202 P203 P204 P205 P206 P207 P208 P209 P210 P211 P212 P213 P214 P215 P216 P217 P218 P219 P220 P221 P222 P223 P224 P225 P226 P227 P228 P229 P230 P210 P211 P229 P230 P240 P25 P26 P27 P27 P28 P29 P29 P29 P210 P211 P218 P219 P219 P219 P219 P220 P221 P221 P222 P223 P224 P225 P226 P227 P228 P229 P230 P230 P230 P230 P230 P230 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P231 P230 P230 P231 P230 P230 P231 P230 P230 P230 P230 P230 P230 P230 P230	NO CONNECT VSS I/O I/O I/O VCC A4_I/O A5_I/O GND I/O A21_I/O A6_I/O A7_I/O VSS VCC A8_I/O A9_I/O A19_I/O A18_I/O I/O I/O GND A11_I/O VCC I/O I/O I/O I/O I/O I/O I/O I

FIGURE 2. <u>Terminal connections</u> - Continued.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 30

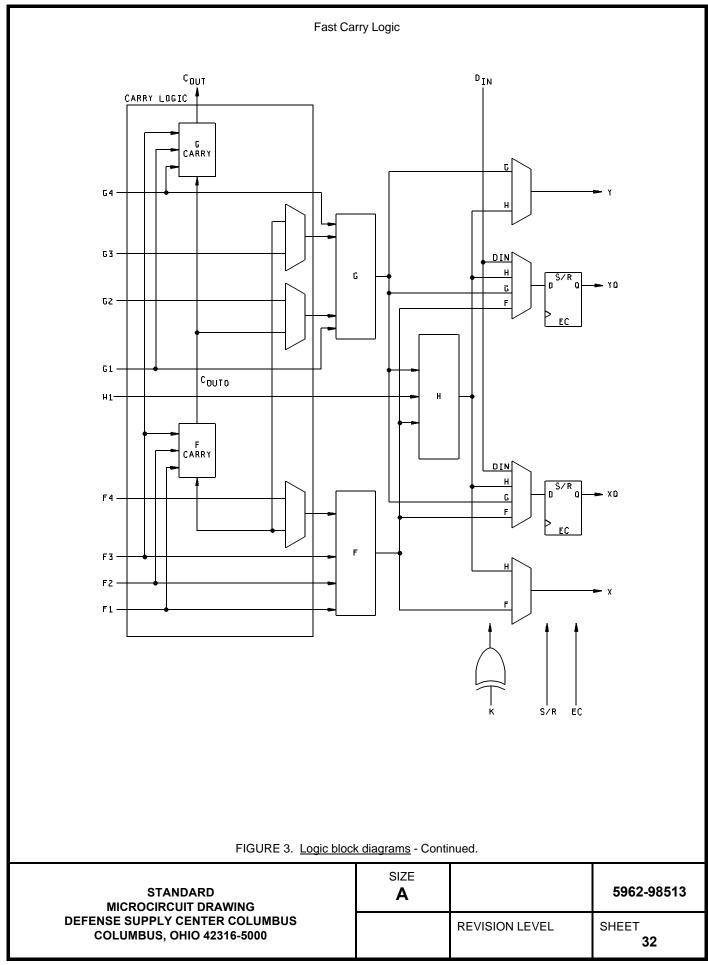
Simplified block diagram of CLB

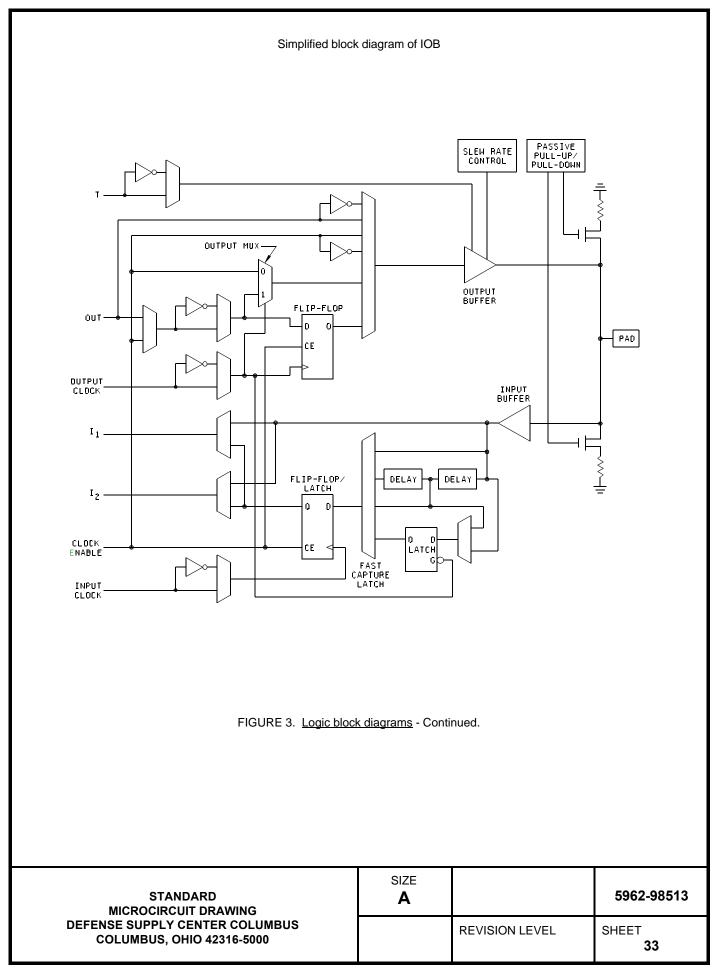


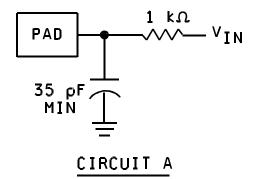
Note: The CLB storage elements can also be configured as latches. The two latches have common clock (CK) and clock enable (EC) inputs. (RAM and Carry logic functions not shown)

FIGURE 3. Logic block diagrams.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 31







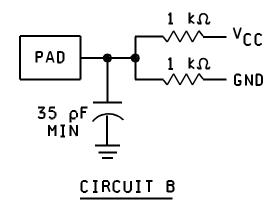


FIGURE 4. Load circuits.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 34

- 4.3 <u>Qualification inspection for device classes N, Q, and V</u>. Qualification inspection for device classes N, Q, and V shall be in accordance with MIL-PRF-38535 and the device manufacturers QM plan. Inspections to be performed shall be those specified in MIL-PRF-38535 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
- 4.4 <u>Conformance inspection</u>. Technology conformance inspection for classes N, Q, and V shall be in accordance with MIL-PRF-38535 including groups A, B, C, D, and E inspections and as specified herein except where option 2 of MIL-PRF-38535 permits alternate in-line control testing. Quality conformance inspection for device class M shall be in accordance with MIL-PRF-38535, appendix A and as specified herein. Inspections to be performed for device class M shall be those specified in method 5005 of MIL-STD-883 and herein for groups A, B, C, D, and E inspections (see 4.4.1 through 4.4.4).
 - 4.4.1 Group A inspection.
 - a. Tests shall be as specified in table IIA herein.
 - b. Subgroups 5 and 6 of table I of method 5005 of MIL-STD-883 shall be omitted.
 - c. For device class M, subgroups 7 and 8 tests shall be sufficient to verify the truth table. For device classes N, Q, and V, subgroups 7 and 8 shall include verifying the functionality of the device; these tests shall have been fault graded in accordance with MIL-STD-883, test method 5012 (see 1.5 herein).
 - d. O/V (latch-up) tests shall be measured only for initial qualification and after any design or process changes which may affect the performance of the device. For device class M, procedures and circuits shall be maintained under document revision level control by the manufacturer and shall be made available to the preparing activity or acquiring activity upon request. For device classes N, Q, and V, the procedures and circuits shall be under the control of the device manufacturer's TRB in accordance with MIL-PRF-38535 and shall be made available to the preparing activity or acquiring activity upon request. Testing shall be on all pins, on five devices with zero failures. Latch-up test shall be considered destructive. Information contained in JEDEC Standard number 17 may be used for reference.
 - e. Subgroup 4 (C_{IN} and C_{OUT} measurements) shall be measured only for initial qualification and after any process or design changes which may affect input or output capacitance. Capacitance shall be measured between the designated terminal and GND at a frequency of 1 MHz. Sample size is 5 devices with no failures, and all input and output terminals tested.
 - (1) The following shall apply to device class N only. Sample size is five devices with no failures. For C_{IN} and C_{OUT} a device manufacturer may qualify devices by functional groups. A specific functional group shall be composed of function types, that by design, will yield the same capacitance values when tested in accordance with table I herein. The device manufacturer shall set a functional group limit for the C_{IN} and C_{OUT} tests. The device manufacturer may then test one device function from a functional group to the limits and conditions specified herein. All other device functions in that particular functional group shall be guaranteed, if not tested, to the limits and conditions specified in table I herein. The device manufacturer shall submit to DSCC-VA the device functions listed in each functional group and the test results for each device tested.
 - 4.4.2 <u>Group C inspection</u>. The group C inspection end-point electrical parameters shall be as specified in table IIA herein.
 - 4.4.2.1 Additional criteria for device class M. Steady-state life test conditions, method 1005 of MIL-STD-883:
 - a. Test condition A or D. The test circuit shall be maintained by the manufacturer under document revision level control and shall be made available to the preparing or acquiring activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.
 - b. $T_A = +125EC$, minimum.
 - c. Test duration: 1,000 hours, except as permitted by method 1005 of MIL-STD-883.
- 4.4.2.2 Additional criteria for device classes N, Q and V. The steady-state life test duration, test condition and test temperature, or approved alternatives shall be as specified in the device manufacturer's QM plan in accordance with MIL-PRF-38535. The test circuit shall be maintained under document revision level control by the device manufacturer's TRB, in accordance with MIL-PRF-38535, and shall be made available to the acquiring or preparing activity upon request. The test circuit shall specify the inputs, outputs, biases, and power dissipation, as applicable, in accordance with the intent specified in test method 1005.

STANDARD MICROCIRCUIT DRAWING	SIZE A		5962-98513
DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000		REVISION LEVEL	SHEET 35

TABLE IIA. Electrical test requirements. 1/2/3/4/5/6/7/

Line no.	Test requirements	Subgroups (in accordance with MIL- STD-883, method 5005, table I)	Subgroups (in accordance with MIL-PRF-38535, table III)		535, table III)
		Device class M	Device class N	Device class Q	Device class V
1	Interin electrical parameters (see 4.2)				1, 7, 9
2	Static burn-in I and II (method 1015)	Required	Not Required	Required	Required
3	Same as line 1				1*, 7*)
4	Dynamic burn-in (method 1015)	Not Required	Not Required	Not Required	Required
5	Same as line 1				1*, 7*)
6	Final electrical parameters	1*, 2, 3, 7*, 8A, 8B, 9, 10, 11	2, 8A, 10	1*, 2, 3, 7*, 8A, 8B, 9, 10, 11	1*, 2, 3, 7*, 8A, 8B, 9, 10, 11
7	Group A test parameters	1, 2, 3, 4**, 7, 8A, 8B, 9, 10, 11	2, 8A, 10	1, 2, 3, 4**, 7, 8A, 8B, 9, 10, 11	1, 2, 3, 4**, 7, 8A, 8B, 9, 10, 11
8	Group C end-point electrical parameters	2, 3, 7, 8A, 8B	1, 2, 3, 7, 8A, 8B	1, 2, 3, 7, 8A, 8B	1, 2, 3, 7, 8A, 8B, 9, 10, 11)
9	Group D end-point electrical parameters	2, 3, 8A, 8B		2, 3, 8A, 8B	2, 3, 8A, 8B
10	Group E end-point electrical parameters	1, 7, 9		1, 7, 9	1, 7, 9

- 1/ Blank spaces indicate tests are not applicable.
 2/ Any or all subgroups may be combined when using high-speed testers.
 3/ Subgroups 7 and 8 functional tests shall verify the truth table.
 4/ * indicates PDA applies to subgroup 1 and 7.
 5/ ** see 4.4.1e.
 6/) indicates delta limit (see table IIB) shall be required where specified, and the delta values shall be computed with reference to the previous interim electrical parameters (see line 1).
- <u>7</u>/ See 4.4.1d.

TABLE IIB. Delta limits at +25

Parameter 1/	Device types	
	All	
ICCO standby	± 1 mA of specified limit in table I.	
IL	± 1 FA of specified limit in table I.	

1/ The above parameter shall be recorded before and after the required burn-in and life tests to determine the delta.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000	SIZE A		5962-98513
		REVISION LEVEL	SHEET 36

- 4.4.3 Group D inspection. The group D inspection end-point electrical parameters shall be as specified in table IIA herein.
- 4.4.4 <u>Group E inspection</u>. Group E inspection is required only for parts intended to be marked as radiation hardness assured (see 3.5 herein).
 - a. End-point electrical parameters shall be as specified in table IIA herein.
 - b. For device classes N, Q, and V, the devices or test vehicle shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535 for the RHA level being tested. For device class M, the devices shall be subjected to radiation hardness assured tests as specified in MIL-PRF-38535, appendix A for the RHA level being tested. All device classes must meet the postirradiation end-point electrical parameter limits as defined in table I at T_A = +25EC ±5EC, after exposure, to the subgroups specified in table IIA herein.
 - c. When specified in the purchase order or contract, a copy of the RHA delta limits shall be supplied.
- 4.5 <u>Delta measurements for device class V.</u> Delta measurements, as specified in table IIA, shall be made and recorded before and after the required burn-in screens and steady-state life tests to determine delta compliance. The electrical parameters to be measured, with associated delta limits are listed in table IIB. The device manufacturer may, at his option, either perform delta measurements or within 24 hours after burn-in perform final electrical parameter tests, subgroups 1, 7, and 9.

5. PACKAGING

5.1 <u>Packaging requirements</u>. The requirements for packaging shall be in accordance with MIL-PRF-38535 for device classes N, Q, and V or MIL-PRF-38535, appendix A for device class M.

6. NOTES

- 6.1 <u>Intended use</u>. Microcircuits conforming to this drawing are intended for use for Government microcircuit applications (original equipment), design applications, and logistics purposes.
- 6.1.1 <u>Replaceability</u>. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.
 - 6.1.2 <u>Substitutability</u>. Device class Q devices will replace device class M devices.
- 6.2 <u>Configuration control of SMD's</u>. All proposed changes to existing SMD's will be coordinated with the users of record for the individual documents. This coordination will be accomplished in accordance with MIL-STD-973 using DD Form 1692, Engineering Change Proposal.
- 6.3 <u>Record of users</u>. Military and industrial users shall inform Defense Supply Center Columbus when a system application requires configuration control and which SMD's are applicable to that system. DSCC will maintain a record of users and this list will be used for coordination and distribution of changes to the drawings. Users of drawings covering microelectronic devices (FSC 5962) should contact DSCC-VA, telephone (614) 692-0525.
- 6.4 <u>Comments</u>. Comments on this drawing should be directed to DSCC-VA, Columbus, Ohio 43216-5000, or telephone (614) 692-0674.
- 6.5 <u>Abbreviations, symbols, and definitions</u>. The abbreviations, symbols, and definitions used herein are defined in MIL-PRF-38535, MIL-HDBK-1331.

V _{CC}	SUPPLY VOLTAGE (V).
GND	GROUND
CCLK	CONFIGURATION CLOCK
DONE	DONE
PROGRAM	PROGRAM
RCLK	READ CLOCK.
M0	MODE 0
M1	MODE 1
M2	MODE 2

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000	SIZE A		5962-98513
		REVISION LEVEL	SHEET 37

6.5 Abbreviations, symbols, and definitions - Continued.

TDO ----- TEST DATA OUTPUT TDI ----- TEST DATA IN TCK ----- TEST CLOCK TMS ----- TEST MODE SELECT HDC ------ HIGH DURING CONFIGURATION ----- LOW DURING CONFIGURATION LDC RTRIG ----- READ TRIGGER. INIT ----- INIT GCK1-GCK8 ------ GLOBALLow-Skew buffer CSO ------ CHIP SELECT, WRITE CS1 ----- CHIP SELECT, WRITE ----- WRITE STROBE WS ----- READ STROBE RS A0-A21 ----- ADDRESS D0-D7 ----- DATA DIN ----- DATA INPUT DOUT ----- DATA OUTPUT ----- INPUT/OUTPUT RDY/BUSY ----- During peripheral parallel mode configuration, this pin indicates when the chip is ready for another byte of data to be written into it. After configuration is complete, this pin becomes a user programmed I/O pin.

6.5.1 <u>Timing limits.</u> The table of timing values shows either a minimum or a maximum limit for each parameter. Input requirements are specified from the external system point of view. Thus, address setup time is shown as a minimum since the system must supply at least that much time (even though most devices do not require it). On the other hand, responses from the memory are specified from the device point of view. Thus, the access time is shown as a maximum since the device never provides data later than that time.

- 6.6 Sources of supply.
- 6.6.1 <u>Sources of supply for device classes N, Q, and V</u>. Sources of supply for device classes N, Q, and V are listed in QML-38535. The vendors listed in QML-38535 have submitted a certificate of compliance (see 3.6 herein) to DSCC-VA and have agreed to this drawing.
- 6.6.2 <u>Approved sources of supply for device class M</u>. Approved sources of supply for class M are listed in MIL-HDBK-103. The vendors listed in MIL-HDBK-103 have agreed to this drawing and a certificate of compliance (see 3.6 herein) has been submitted to and accepted by DSCC-VA.
 - 6.7 Additional operating data.
 - a. Power on delay is 2¹⁴ cycles from the non-master mode. This provides 11 to 33 ms of wait time.
 - b. Power on delay is 2^{16} cycles for the master mode. This provides 43 to 130 ms of wait time.
 - c. Clear is 375 cycles ± 25 cycles and may take as long as 250 to 750 μ s.
 - d. During normal power up, V_{CC} must rise from 2.0 V to V_{CC} minimum in less than 10 ms. If this does not occur, configuration must be delayed by using RESET.

STANDARD MICROCIRCUIT DRAWING DEFENSE SUPPLY CENTER COLUMBUS COLUMBUS, OHIO 42316-5000	SIZE A		5962-98513
		REVISION LEVEL	SHEET 38

STANDARD MICROCIRCUIT DRAWING SOURCE APPROVAL BULLETIN

DATE: 98-12-16

Approved sources of supply for SMD 5962-98513 are listed below for immediate acquisition only and shall be added to QML-38535 and MIL-HDBK-103 during the next revisions. QML-38535 and MIL-HDBK-103 will be revised to include the addition or deletion of sources. The vendors listed below have agreed to this drawing and a certificate of compliance has been submitted to and accepted by DSCC-VA. This bulletin is superseded by the next dated revisions of QML-38535 and MIL-HDBK-103.

Standard microcircuit drawing PIN <u>1</u> /	Vendor CAGE number	Vendor similar PIN <u>2</u> /
5962-9851301QXC	68994	XQ4013XL-3PG223B
5962-9851301QYC	68994	XQ4013XL-3CB228B
5962-9851301QZC	68994	XQ4013XL-3CB228B
5962-9851301NUA	<u>3</u> /	XQ4013XL-3G256N
5962-9851301NTB	68994	XQ4013XL-3PQ240N

- 1/ The lead finish shown for each PIN representing a hermetic package is the most readily available from the manufacturer listed for that part. If the desired lead finish is not listed contact the vendor to determine its availability.
- 2/ <u>Caution</u>. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.
- 3/ Not available at time of document release, should be available 1st quarter of 1999.

Vendor CAGE
numberVendor name
and address68994Xilinx, Incorporated

2100 Logic Drive San Jose, CA 95124

The information contained herein is disseminated for convenience only and the Government assumes no liability whatsoever for any inaccuracies in this information bulletin.